

*A*

region, which is of the first conductivity type, which forms an emitter region of the transistor, and which is provided with a third connection conductor, and whereby the device is provided with means for preventing a saturation of the transistor during normal use, characterized in that the second connection conductor is exclusively connected to the second semiconductor region for preventing a saturation of the transistor, and in that a partial region of that portion of the second semiconductor region which lies outside the third semiconductor region, as seen in projection, and adjacent the second connection conductor is provided with a smaller flux of dopant atoms.

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7. (Amended) A method as claimed in claim 6, characterized in that the partial region of the second semiconductor region is formed below the second connection conductor and is given a smaller thickness and a lower doping concentration.

8. (Amended) A method as claimed in claim 6, characterized in that the partial region of the second semiconductor region is given a smaller thickness.

9. (Amended) A method as claimed in claim 6, characterized in that the partial region of the second semiconductor region is formed by means of ion implantation.

*Sub C5*

10. (Amended) A method as claimed in claim 6, characterized in that a thin, strongly doped fourth semiconductor region of the first conductivity type is formed between the partial region of the second semiconductor region and the second connection conductor, preferably simultaneously with the third semiconductor region.